VP3203

P-Channel Enhancement-Mode Vertical DMOS FET

Features

- Free from Secondary Breakdown
- Low Power Drive Requirement
- Ease of Paralleling
- Low C_{ISS} and Fast Switching Speeds
- Excellent Thermal Stability
- Integral Source-to-Drain Diode
- High Input Impedance and High Gain

Applications

- Motor Controls
- Converters
- Amplifiers
- Switches
- Power Supply Circuits
- Drivers (Relays, Hammers, Solenoids, Lamps, Memories, Displays, Bipolar Transistors, etc.)

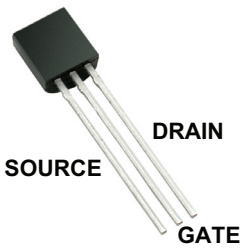
General Description

The VP3203 Enhancement-mode (normally-off) transistor uses a vertical DMOS structure and a well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally induced secondary breakdown.

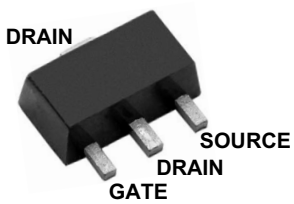
Microchip's vertical DMOS FETs are ideally suited for a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Package Types

3-lead TO-92
(Top view)



3-lead SOT-89
(Top view)



See Table 3-1 and Table 3-2 for pin information.

1.0 ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings†

Drain-to-Source Voltage ..... BV_{DSS}
Drain-to-Gate Voltage ..... BV_{DGS}
Gate-to-Source Voltage ..... ±20V
Operating Ambient Temperature, T_A ..... –55°C to +150°C
Storage Temperature, T_S ..... –55°C to +150°C

† Notice: Stresses above those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at those or any other conditions above those indicated in the operational sections of this specification is not intended. Exposure to maximum rating conditions for extended periods may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

Electrical Specifications: T_A = 25°C unless otherwise specified. All DC parameters are 100% tested at 25°C unless otherwise stated. Pulse test: 300 µs pulse, 2% duty cycle

Parameter		Sym.	Min.	Typ.	Max.	Unit	Conditions
Drain-to-Source Breakdown Voltage		BV_{DSS}	–30	—	—	V	V_{GS} = 0V, I_D = –10 mA
Gate Threshold Voltage		$V_{GS(th)}$	–1	—	–3.5	V	V_{GS} = V_{DS}, I_D = –10 mA
Change in $V_{GS(th)}$ with Temperature		$\Delta V_{GS(th)}$	—	—	–5.5	mV/°C	V_{GS} = V_{DS}, I_D = –10 mA (**Note 1**)
Gate Body Leakage Current		I_{GSS}	—	–1	–100	nA	V_{GS} = ± 20V, VDS = 0V
Zero-Gate Voltage Drain Current		I_{DSS}	—	—	–10	µA	V_{GS} = 0V, V_{DS} = Maximum rating
			—	—	–1	mA	V_{DS} = 0.8 Maximum rating, V_{GS} = 0V, T_A = 125°C (**Note 1**)
On-State Drain Current		$I_{D(ON)}$	—	–14	—	A	V_{GS} = –10V, V_{DS} = –5V
Static Drain-to-Source On-State Resistance	TO-92	$R_{DS(ON)}$	—	—	1	Ω	V_{GS} = –4.5V, I_D = –1.5A
	SOT-89		—	—	1	Ω	V_{GS} = –4.5V, I_D = –750 mA
	TO-92		—	—	0.6	Ω	V_{GS} = –10V, I_D = –3A
	SOT-89		—	—	0.6	Ω	V_{GS} = –10V, I_D = –1.5A
Change in $R_{DS(ON)}$ with Temperature		$\Delta R_{DS(ON)}$	—	—	1	%/°C	V_{GS} = –10V, I_D = –1.5A (**Note 1**)

Note 1: Specification is obtained by characterization and is not 100% tested.

AC ELECTRICAL CHARACTERISTICS

Electrical Specifications: T_A = 25°C unless otherwise specified. All AC parameters are not 100% sample tested.						
Parameter	**Sym.**	**Min.**	**Typ.**	**Max.**	**Unit**	**Conditions**
Forward Transconductance	G_{FS}	1000	2000	—	mmho	V_{DS} = –25V, I_D = –2A
Input Capacitance	C_{ISS}	—	200	300	pF	V_{GS} = 0V, V_{DS} = -25V, f = 1 MHz
Common-Source Output Capacitance	C_{OSS}	—	100	120	pF	
Reverse Transfer Capacitance	C_{RSS}	—	45	60	pF	
Turn-On Delay Time	$t_{d(ON)}$	—	—	10	ns	V_{DD} = -25V, I_D = –2A, R_{GEN} = 10Ω
Rise Time	t_r	—	—	15	ns	
Turn-Off Delay Time	$t_{d(OFF)}$	—	—	25	ns	
Fall Time	t_f	—	—	25	ns	
DIODE PARAMETER						
Diode Forward Voltage Drop	V_{SD}	—	—	–1.6	V	V_{GS} = 0V, I_{SD} = –1.5A (**Note 1**)
Reverse Recovery Time	t_{rr}	—	300	—	ns	V_{GS} = 0V, I_{SD} = –1A

Note 1: Unless otherwise stated, all DC parameters are 100% tested at 25°C. Pulse test: 300 µs pulse, 2% duty cycle

TEMPERATURE SPECIFICATIONS

Parameter	**Sym.**	**Min.**	**Typ.**	**Max.**	**Unit**	**Conditions**
TEMPERATURE RANGE						
Operating Ambient Temperature	T_A	–55	—	+150	°C	
Storage Temperature	T_S	–55	—	+150	°C	
PACKAGE THERMAL RESISTANCE						
3-lead TO-92	θ_{JA}	—	132	—	°C/W	
3-lead SOT-89	θ_{JA}	—	133	—	°C/W	

THERMAL CHARACTERISTICS

Package	**I_D (Note 1) (Continuous) (mA)**	**I_D (Pulsed) (A)**	**Power Dissipation at T_A = 25°C (W)**	**I_{DR} (Note 1) (mA)**	**I_{DRM} (A)**
3-lead TO-92	–650	–4	0.74	–650	–4
3-lead SOT-89	–1100	–4	1.6 (**Note 2**)	–1100	–4

Note 1: I_D (continuous) is limited by maximum rated T_J.

2: Mounted on an FR board 25 mm x 25 mm x 1.57 mm.

2.0 TYPICAL PERFORMANCE CURVES

Note: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g. outside specified power supply range) and therefore outside the warranted range.

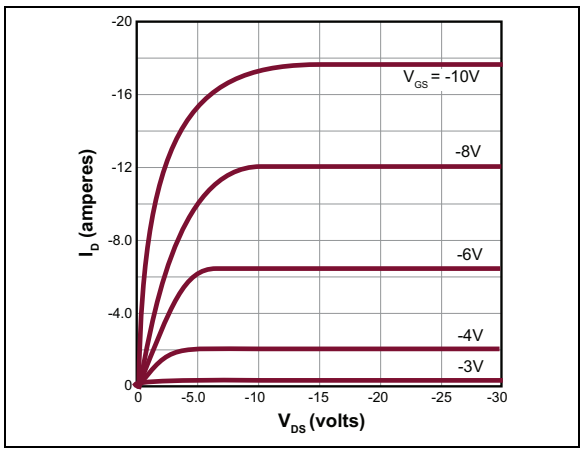


FIGURE 2-1: *Output Characteristics.*

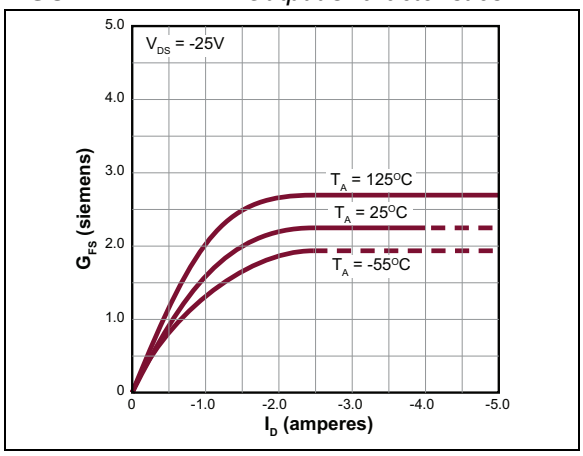


FIGURE 2-2: *Transconductance vs. Drain Current.*

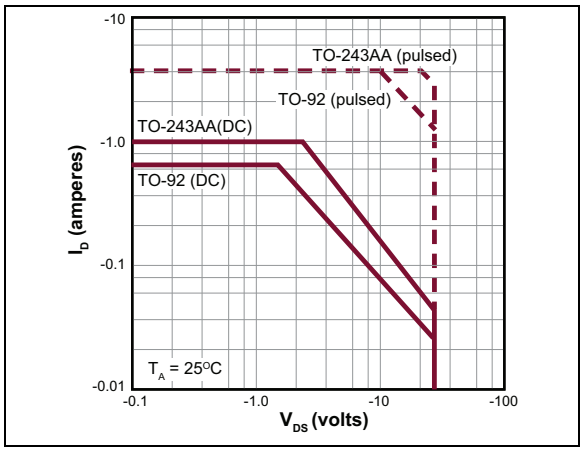


FIGURE 2-3: *Maximum Rated Safe Operating Area.*

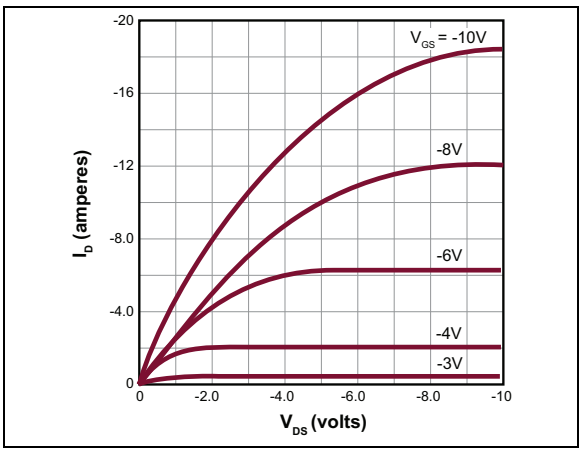


FIGURE 2-4: *Saturation Characteristics.*

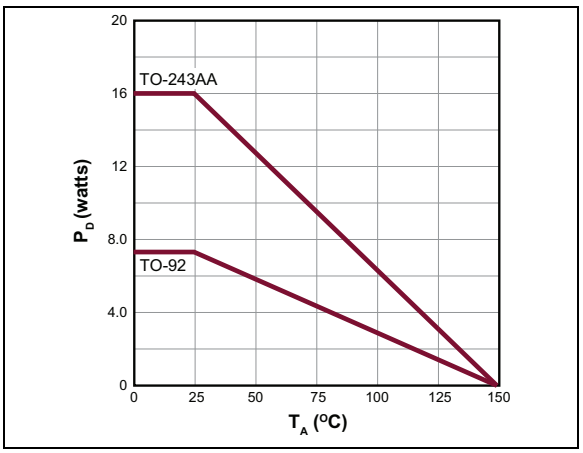


FIGURE 2-5: *Power Dissipation vs. Case Temperature.*

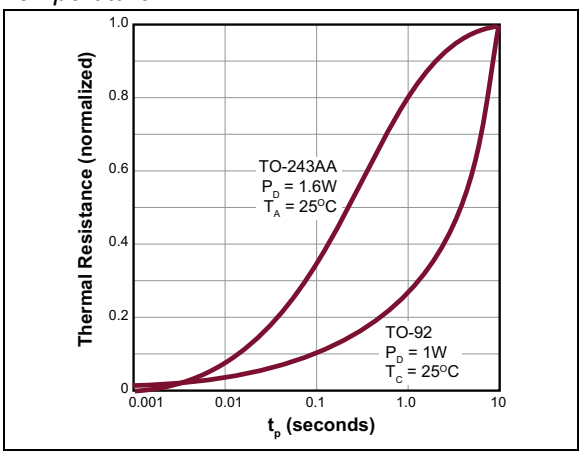


FIGURE 2-6: *Thermal Response Characteristics.*

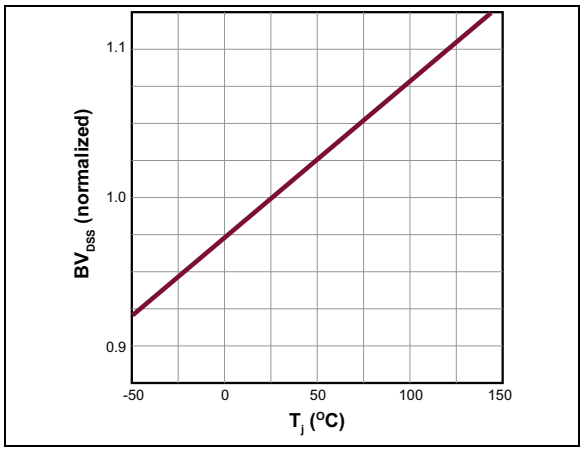


FIGURE 2-7: *BV_{DSS} Variation with Temperature.*

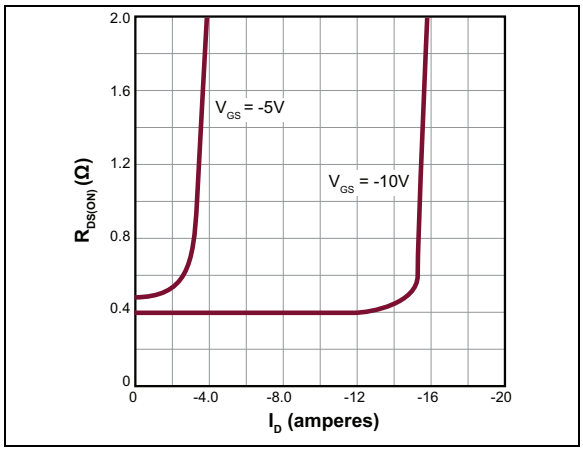


FIGURE 2-10: *On-Resistance vs. Drain Current.*

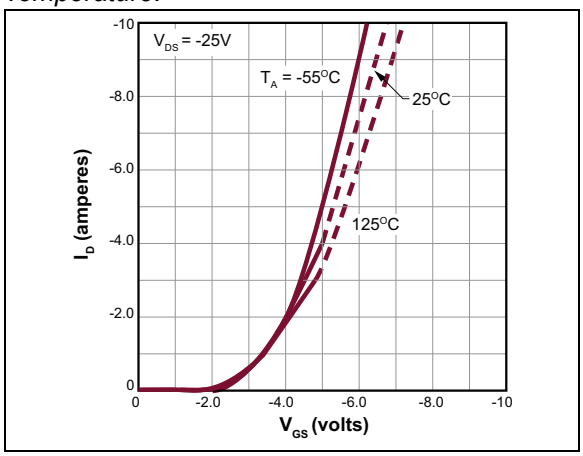


FIGURE 2-8: *Transfer Characteristics.*

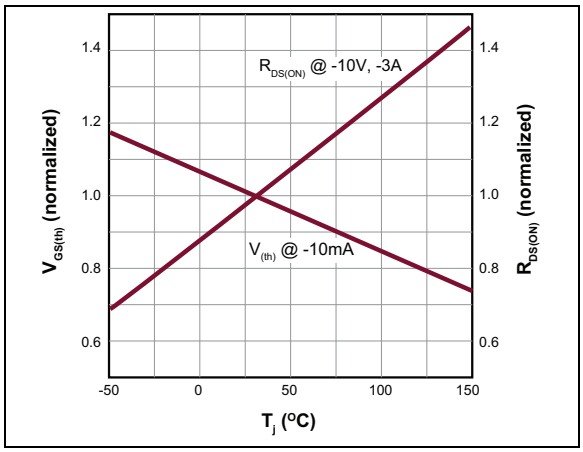


FIGURE 2-11: *$V_{(th)}$ and R_{DS} Variation with Temperature.*

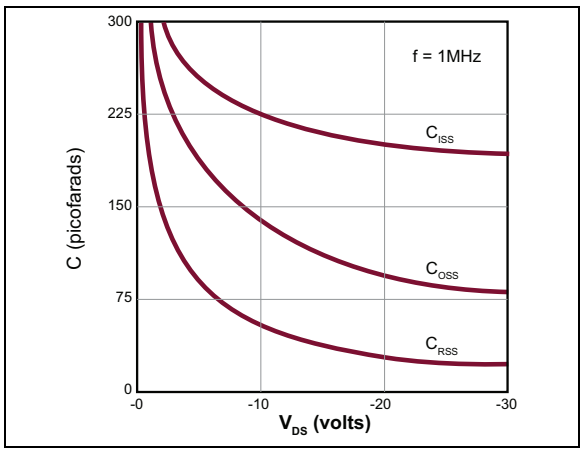


FIGURE 2-9: *Capacitance vs. Drain-to-Source Voltage.*

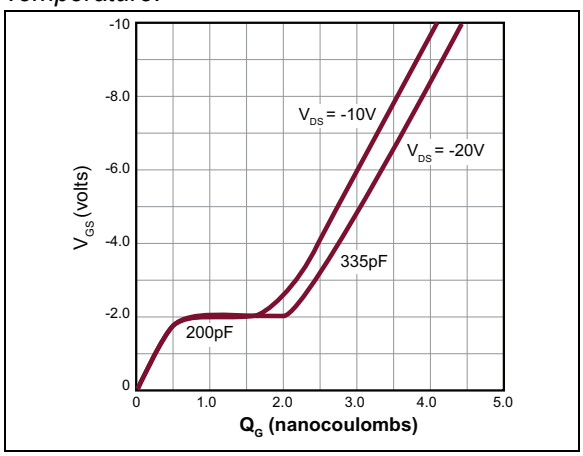


FIGURE 2-12: *Gate Drive Dynamic Characteristics.*

3.0 PIN DESCRIPTION

The details on the pins of VP3203 3-lead TO-39 and 3-lead SOT-89 are listed in Table 3-1 and Table 3-2, respectively. Refer to **Package Types** for the location of pins.

TABLE 3-1: 3-LEAD TO-39 PIN FUNCTION TABLE

Pin Number	Pin Name	Description
1	Source	Source
2	Gate	Gate
3	Drain	Drain

TABLE 3-2: 3-LEAD SOT-89 PIN FUNCTION TABLE

Pin Number	Pin Name	Description
1	Gate	Gate
2,4	Drain	Drain
3	Source	Source

4.0 FUNCTIONAL DESCRIPTION

Figure 4-1 illustrates the switching waveforms and test circuit for VP3203.

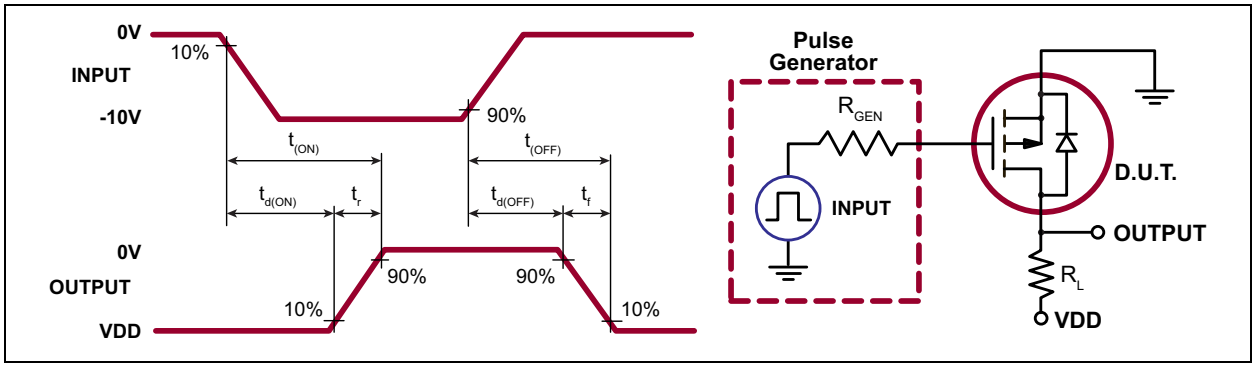


FIGURE 4-1: *Switching Waveforms and Test Circuit.*

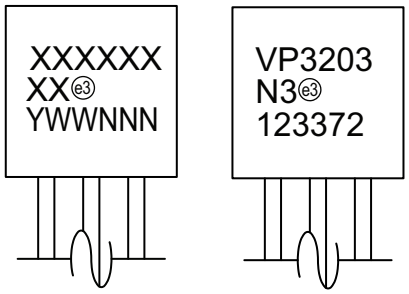
TABLE 4-1: PRODUCT SUMMARY

BV_{DSS}/BV_{DGS} (V)	$R_{DS(ON)}$ (Maximum) (Ω)	$I_{D(ON)}$ (Minimum) (A)
–30	0.6	–4

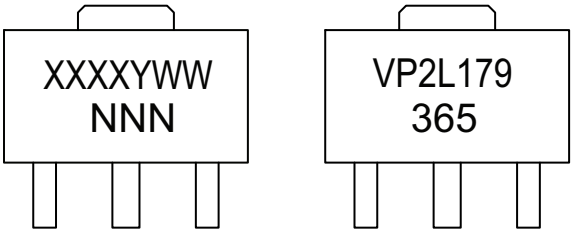
5.0 PACKAGING INFORMATION

5.1 Package Marking Information

3-lead TO-92 Example



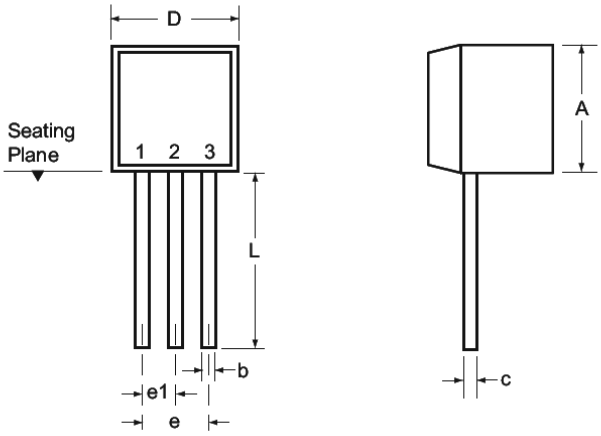
3-lead SOT-89 Example



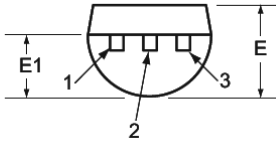
Legend:	XX...X	Product Code or Customer-specific information
	Y	Year code (last digit of calendar year)
	YY	Year code (last 2 digits of calendar year)
	WW	Week code (week of January 1 is week ‘01’)
	NNN	Alphanumeric traceability code
	(e3)	Pb-free JEDEC® designator for Matte Tin (Sn)
	*	This package is Pb-free. The Pb-free JEDEC designator ((e3)) can be found on the outer packaging for this package.

Note: In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for product code or customer-specific information. Package may or not include the corporate logo.

3-Lead TO-92 Package Outline (L/LL/N3)



Front View **Side View**



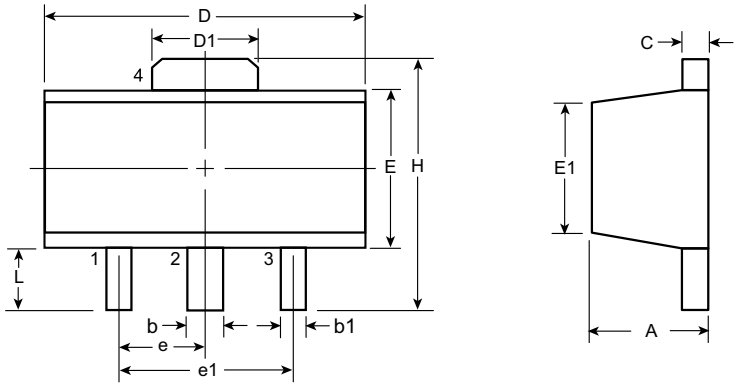
Bottom View

Note: For the most current package drawings, see the Microchip Packaging Specification at www.microchip.com/packaging.

Symbol		A	b	c	D	E	E1	e	e1	L
Dimensions (inches)	MIN	.170	.014†	.014†	.175	.125	.080	.095	.045	.500
	NOM	-	-	-	-	-	-	-	-	-
	MAX	.210	.022†	.022†	.205	.165	.105	.105	.055	.610*

JEDEC Registration TO-92.
** This dimension is not specified in the JEDEC drawing.*
† This dimension differs from the JEDEC drawing.
Drawings not to scale.

3-Lead TO-243AA (SOT-89) Package Outline (N8)



Top View **Side View**

Note: For the most current package drawings, see the Microchip Packaging Specification at www.microchip.com/packaging.

Symbol		A	b	b1	C	D	D1	E	E1	e	e1	H	L
Dimensions (mm)	MIN	1.40	0.44	0.36	0.35	4.40	1.62	2.29	2.00†	1.50 BSC	3.00 BSC	3.94	0.73†
	NOM	-	-	-	-	-	-	-	-			-	-
	MAX	1.60	0.56	0.48	0.44	4.60	1.83	2.60	2.29			4.25	1.20

JEDEC Registration TO-243, Variation AA, Issue C, July 1986.
† This dimension differs from the JEDEC drawing
***Drawings not to scale**.*

APPENDIX A: REVISION HISTORY

Revision A (December 2021)

- Converted Supertex Doc# DSFP-VP3203 to Microchip DS20006013A
- Changed the package marking format
- Removed the 3-lead TO-92 N3 P002, P003, P005, P013, and P014 media types to align packaging specifications with the actual BQM
- Added some sections to comply with the standard Microchip format
- Made minor text changes throughout the document

PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, contact your local Microchip representative or sales office.

PART NO.	XX	-	X	-	X
Device	Package Options		Environmental		Media Type

Device:	VP3203	=	P-Channel Enhancement-Mode Vertical DMOS FET
Packages:	N3	=	3-lead TO-92
	N8	=	3-lead SOT-89
Environmental:	G	=	Lead (Pb)-free/RoHS-compliant Package
Media Types:	(blank)	=	1000/Bag for an N3 Package
	(blank)	=	2000/Reel for an N8 Package

Examples:

a) VP3203N3-G:	P-Channel Enhancement-Mode, Vertical DMOS FET, 3-lead TO-92, 1000/Bag
b) VP3203N8-G:	P-Channel Enhancement-Mode, Vertical DMOS FET, 3-lead SOT-89, 2000/Reel

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